Supplementary Information

Piezoresistive response of quasi one-dimensional ZnO nanowires using an *in situ* electromechanical device

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Figure S1

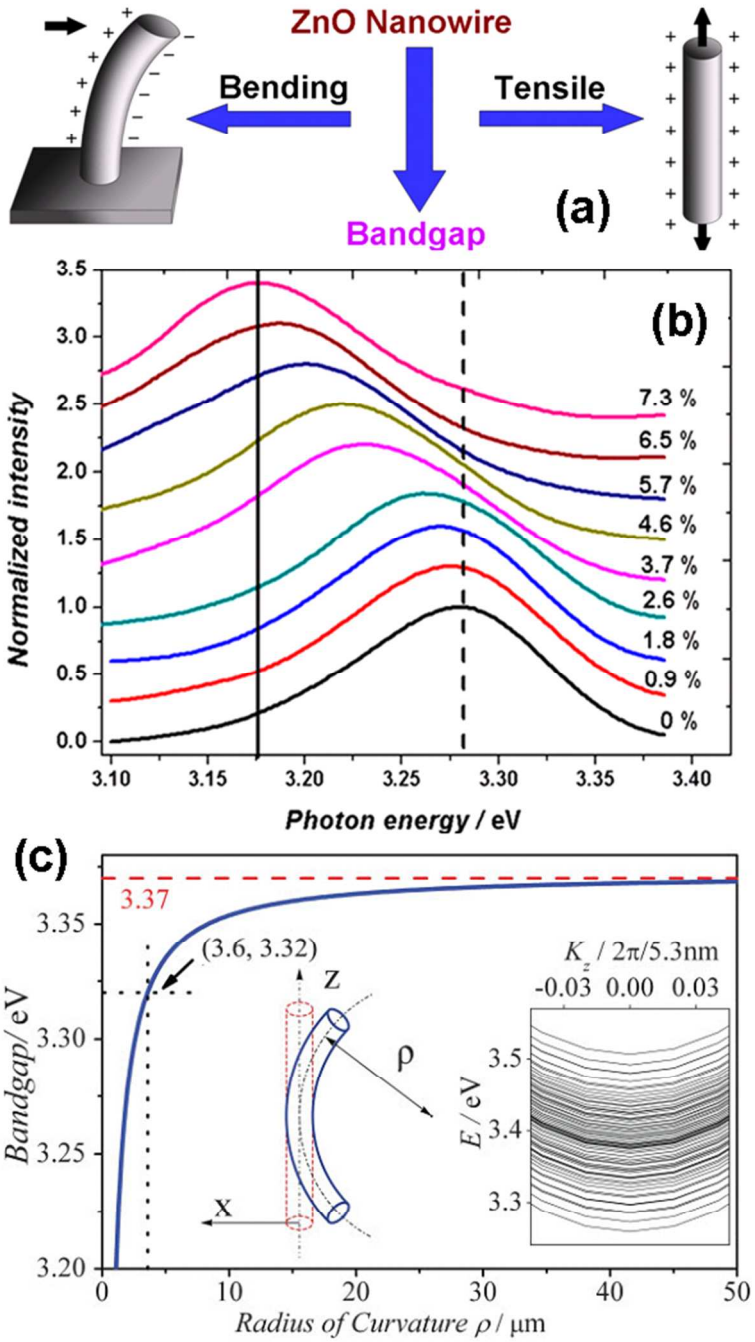

Figure S1: (a) Schematics demonstrating distribution of charge carriers in ZnO nanowires under mechanical deformations (left-bending, right-tensile). (b) Increase in the band gap as radius of curvature of a bending ZnO nanowire (c) Near band exciton (NBE) emission (photoluminescence) series from a ZnO nanowire (100 nm diameter) under (tensile) loading process showing the decrease in bandgap under tension. [With copyright permission from (b) Han *et al.,* Adv. Mater. 21, 2009, 4937–4941 & (c) Bin Wei *et al.,* Nano Letters 12, 2012, 4595−4599].